

# Isc N-Channel MOSFET Transistor

# STP20NM60

**• FEATURES**

- Typical  $R_{DS(on)}=0.25 \Omega$
- Low input capacitance and gate charge
- Low gate input resistances
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**• APPLICATIONS**

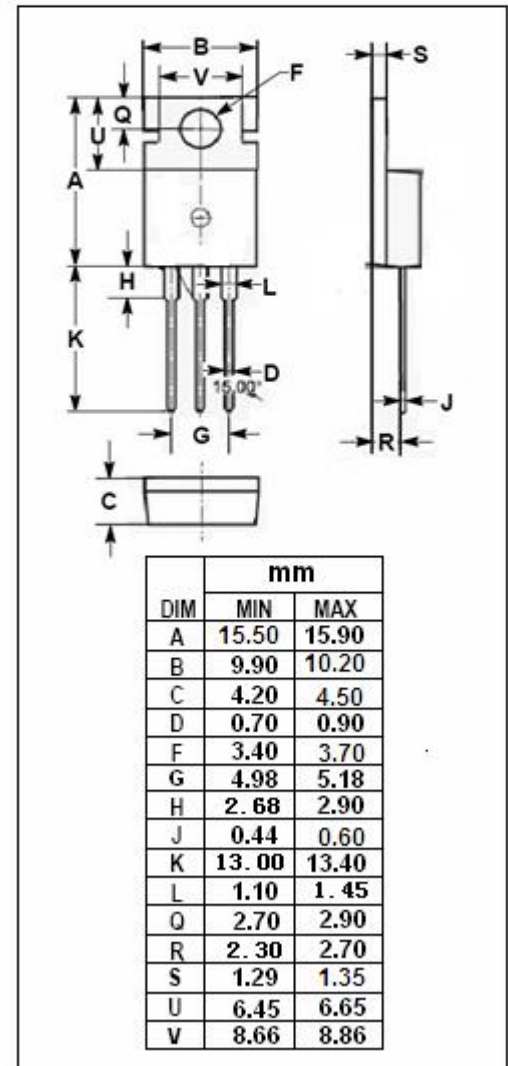
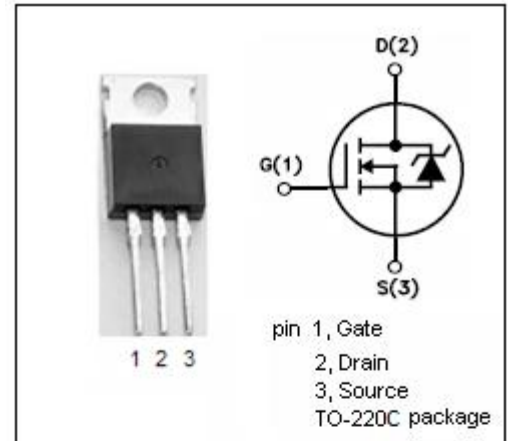
- Suitable for increasing power density of high voltage converters allowing system miniaturization
- High efficiencies.

**• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	600	V
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-Continuous@ $T_c=25^\circ C$ $T_c=100^\circ C$	20 12.6	A
$I_{DM}$	Drain Current-Single Pulsed	80	A
$P_D$	Total Dissipation	192	W
$T_j$	Operating Junction Temperature	-65~150	$^\circ C$
$T_{stg}$	Storage Temperature	-65~150	$^\circ C$

**• THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.65	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62.5	$^\circ C/W$



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**ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA	600			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =±30V; I <sub>D</sub> =0.25mA	3		5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =10A		250	290	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V; T <sub>J</sub> =25°C T <sub>J</sub> =125°C			1 10	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =20A, V <sub>GS</sub> = 0 V			1.5	V